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Vishay Siliconix

# Automotive N-Channel 20 V (D-S) 175 °C MOSFET

# SOT-23 (TO-236)



Marking Code: 9PYXX

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	20				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.030				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 2.5 \text{ V}$	0.034				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 1.8 \text{ V}$	0.038				
I <sub>D</sub> (A)	6				
Configuration	Single				

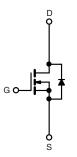
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



N.Channal	MOCEET

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2310CES (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		$V_{DS}$	20	V
Gate-source voltage		$V_{GS}$	± 8	V
Continuous drain current	T <sub>C</sub> = 25 °C	1	6	
	T <sub>C</sub> = 125 °C	l <sub>D</sub>	3.5	
Continuous source current (diode conduction)		I <sub>S</sub>	2.5	Α
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	24	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	10	
Single pulse avalanche energy	L = U.1 MH	E <sub>AS</sub>	5	mJ
Maximum power dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	2	W
	T <sub>C</sub> = 125 °C		0.6	
Operating junction and storage temperature	e range	T <sub>J</sub> , T <sub>stq</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount b	R <sub>thJA</sub>	175	°C/W		
Junction-to-foot (drain)		$R_{thJF}$	75	- C/VV		

### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR-4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static				l		•	·
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		20	-	-	.,
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		0.6	1	V
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$		-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V, T <sub>J</sub> = 175 °C	-	-	150	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = 4.5 V	V <sub>DS</sub> ≥ 5 V	10	-	-	Α
	, ,	V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 5 A	-	0.022	0.030	
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 5 A, T <sub>J</sub> = 125 °C	-	-	0.043	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5V$	I <sub>D</sub> = 5 A, T <sub>J</sub> = 175 °C	-	-	0.051	Ω
	. ,	V <sub>GS</sub> = 2.5 V	I <sub>D</sub> = 4 A	-	0.025	0.034	
		V <sub>GS</sub> = 1.8 V	I <sub>D</sub> = 3.6 A	-	0.029	0.038	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 4 A	-	25	-	S
Dynamic <sup>b</sup>				l		•	<u> </u>
Input capacitance	C <sub>iss</sub>			-	426	590	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	<sub>GS</sub> = 0 V V <sub>DS</sub> = 10 V, f = 1 MHz	-	106	140	pF
Reverse transfer capacitance	$C_{rss}$	1		-	52	70	
Total gate charge <sup>c</sup>	Qg			-	4.95	8.5	nC
Gate-source charge <sup>c</sup>	$Q_{gs}$	$V_{GS} = 4.5 \text{ V}$	$V_{DS} = 10 \text{ V}, I_{D} = 5 \text{ A}$	-	0.65	-	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>	1		-	0.93	-	
Gate resistance	$R_g$	f = 1 MHz		4	9.4	16	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	6	11	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$= 10 \text{ V}, \text{ R}_{\text{L}} = 2.5 \Omega$	=.	19	30	]
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 4 \text{ A}, V$	$I_D \cong 4$ Å, $V_{GEN} = 4.5$ V, $R_g = 1$ $\Omega$		29	45	ns
Fall time <sup>c</sup>	t <sub>f</sub>	1			6	10	
Source-Drain Diode Ratings and Character	eristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	24	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	I <sub>F</sub> = 2.8 A, V <sub>GS</sub> = 0 V		0.70	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 4 A, di/dt = 100 A / μs		-	7	14	ns
Body diode reverse recovery charge	Qrr			-	2	4	nC
Reverse recovery fall time	t <sub>a</sub>			-	7	-	
Reverse recovery rise time	t <sub>b</sub>			-	3	-	ns
Body diode peak reserve recovery current	I <sub>RM(REC)</sub>			-	-0.6	-	Α

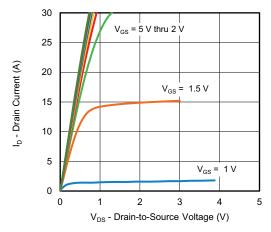
### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

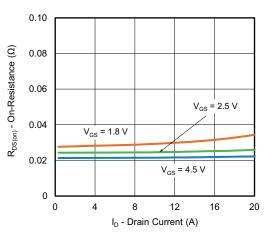
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



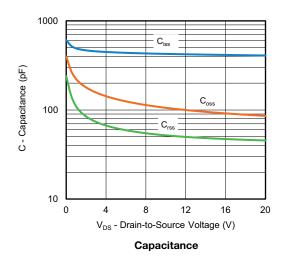
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

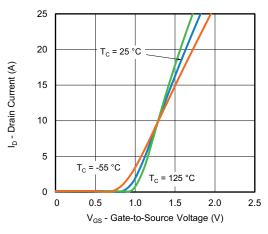


### **Output Characteristics**

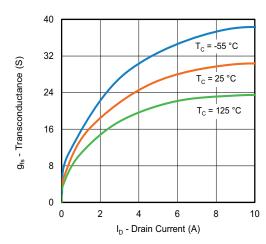


On-Resistance vs. Drain Current

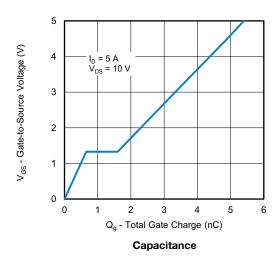




### **Transfer Characteristics**

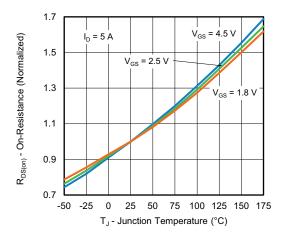


Transconductance

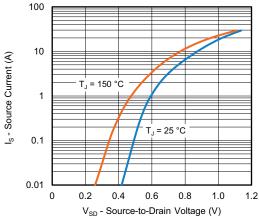




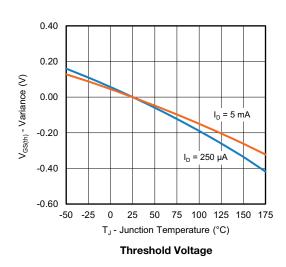
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

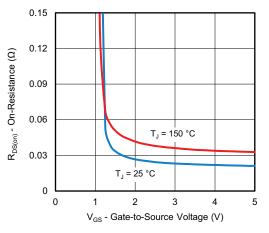


On-Resistance vs. Junction Temperature

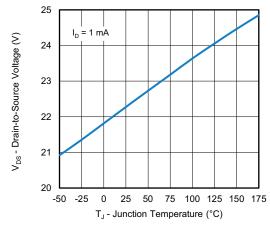


Source Drain Diode Forward Voltage

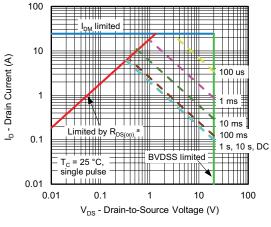




On-Resistance vs. Gate-to-Source Voltage



**Drain Source Breakdown vs. Junction Temperature** 



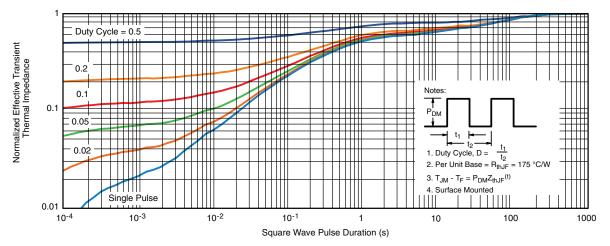
Safe Operating Area

#### Note

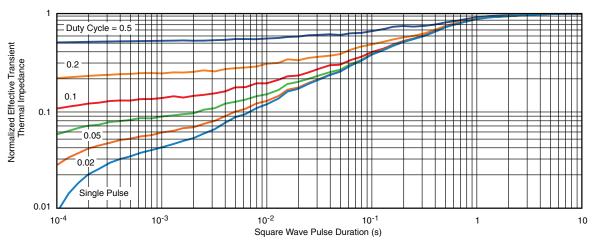
a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(ON)}$  is specified



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

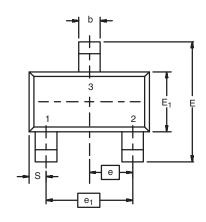
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

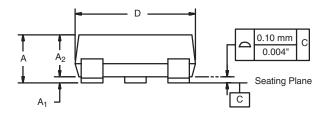
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

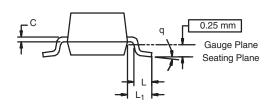
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?62145">www.vishay.com/ppg?62145</a>.

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# SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
FCN: S-03946-Rev K 09-	lul-01	•			

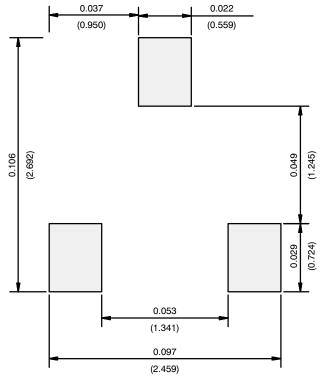
ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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